SOP-8 P

Dual P-CHANNEL MOSFET in a SOP-8 Plastic Package .

Dual P-CHANNEL

VDS(V)=-30V

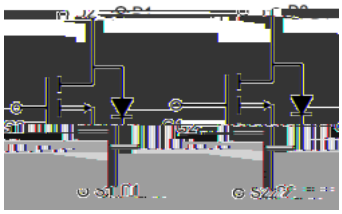
ID=-7.1A

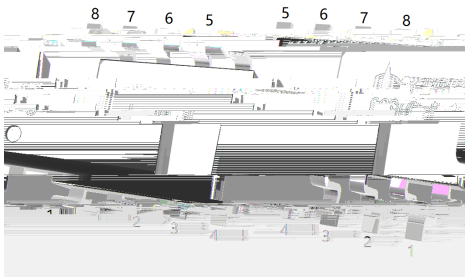
RDS(ON)<22mΩ(VGS=-10V)

RDS(ON)<35mΩ(VGS=-4.5V)

HF Product.

Power Management in Notebook Computer,Portable Equipment and Battery Powered Systems.





PIN1 S1 PIN 2 G1 PIN 3 S2 PIN 4 G2

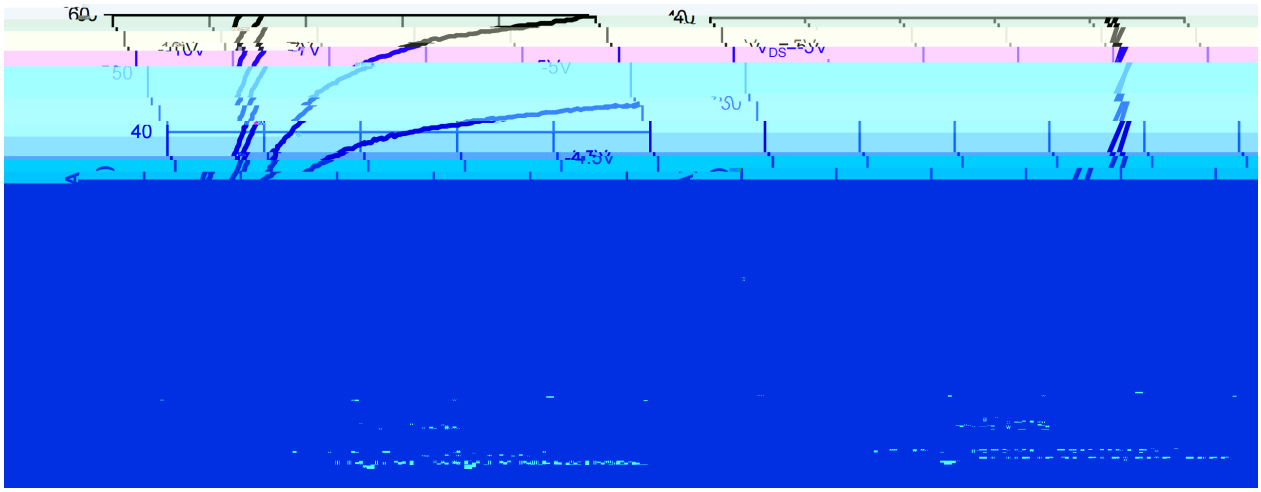
PIN 5 D2 PIN 6 D2 PIN 7 D1 PIN 8 D1

See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Drain Current - Continuous		I_D	-7.1	A
Drain Current – Pulsed		I_{DM}	-40	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		P_D	2	W
Single Pulse Avalanche Energy(L=0.5mH)		E_{AS}	152	mJ
Avalanche Current(L=0.5mH)		I_{AS}	-19.5	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	62.5	Ņ / W
	Steady-State		90	
Thermal resistance, junction - Lead	Steady-State	$R_{\theta JL}$	40	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA V_{GS}=0V	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V V_{GS}=0V			-1	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS I_D=-250μA	-1	-1.3	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A		20	22	mΩ
		V_{GS}=-4.5V, I_D=-10A		28	35	
Diode Forward Voltage	V_{SD}	I_S=-1A, V_{GS}=0V			-1.2	V
Input Capacitance	C_{iss}	V_{DS}=-25V V				

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-15V R_L=0.75Ω R_{GEN}=3Ω		11		ns
Turn-On Rise Time	t_r			5.6		
Turn-Off Delay Time	$t_{d(off)}$			28		
Turn-Off Fall Time	t_f			11		


60
40
40
40
1.8
35
10
0.8
Temperature (℃)
Gate Voltage
60
50
I_D=-20A
1.0E+02

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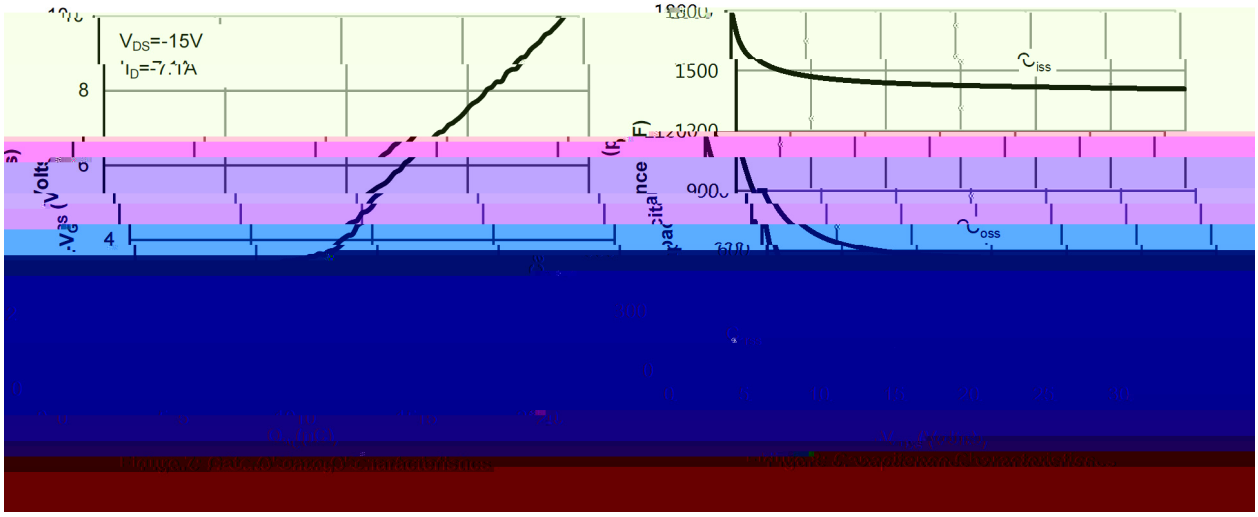
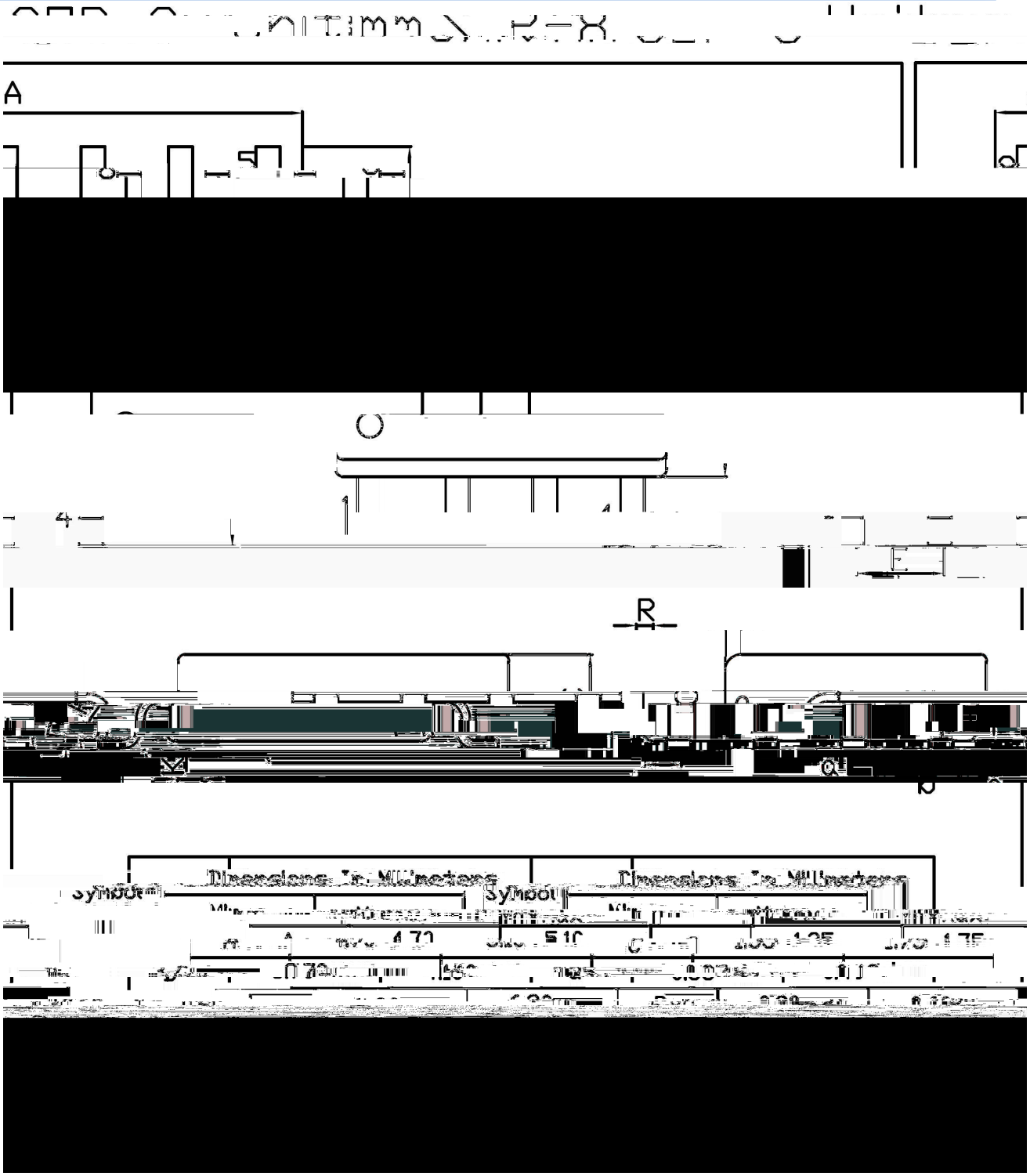

VDS=-15V
ID=-7.1A
8
6
4
1500
Ciss
Coss


A
R
Dimensions In Millimeters
Symbol
Dimensions In Millimeters

Temperature Profile for IR Reflow Soldering(Pb-Free)

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